

From Back-to-Back to Monolithic: The Role of GaN BDS in Next-Generation Power Electronics

*Marco Ruggeri,
Snr. Manager Power System Architecture, Renesas*

**Bodo's
Wide Bandgap
Event 2025**

Making WBG Designs Happen

GaN

AGENDA

- INTRODUCTION: BDS GaN OVERVIEW
- BDS GaN BASED MICRO-INVERTER
- BDS GaN BASED VIENNA RECTIFIER
- CONCLUSION



INTRODUCTION: BDS GAN OVERVIEW

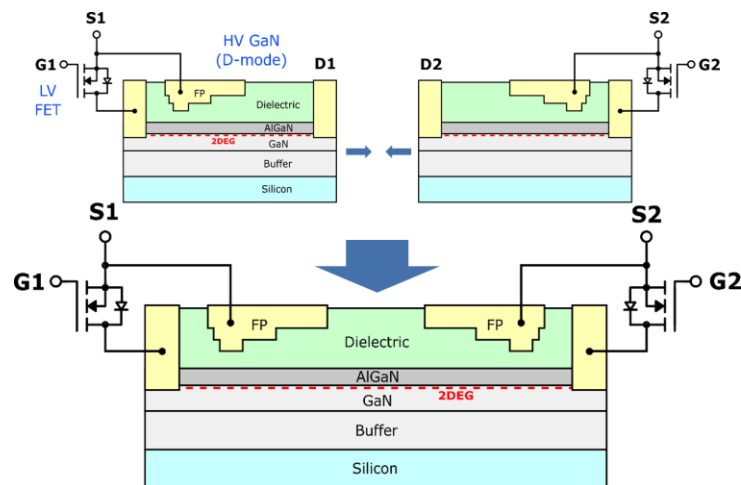
RENESAS



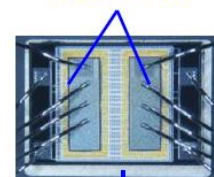
MONOLITHIC BDS WITH D-MODE GAN OVERVIEW

Bidirectional GaN Cascode enables:

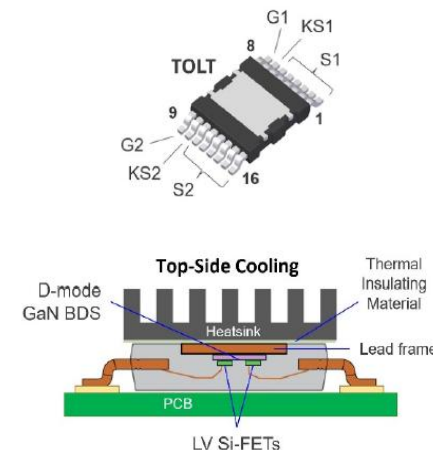
- Monolithic HV GaN achieving low $R_{on,sp}$
- High and stable V_{th} (3V)
- AC and DC blocking capability
- High di/dt & dV/dt immunity



LV Si-FETs



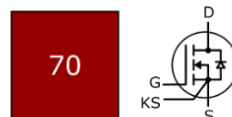
HV D-mode
GaN BDS



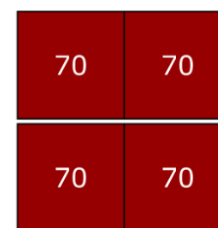
System Level Benefits:

- Improve solution size and cost
- Improve reliability by reducing number of active components
- Improve system efficiency

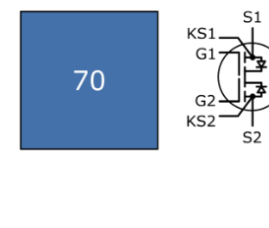
70 mΩ
unidirectional
1x chip area



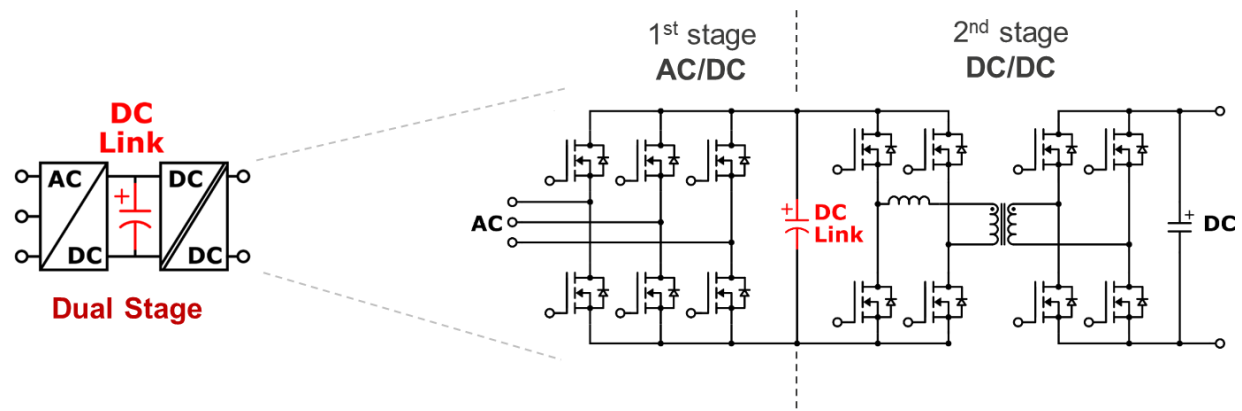
70 mΩ
bidirectional
back-to-back
4x chip area



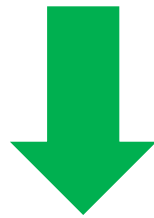
70 mΩ
bidirectional
integrated
≤1.8x chip area



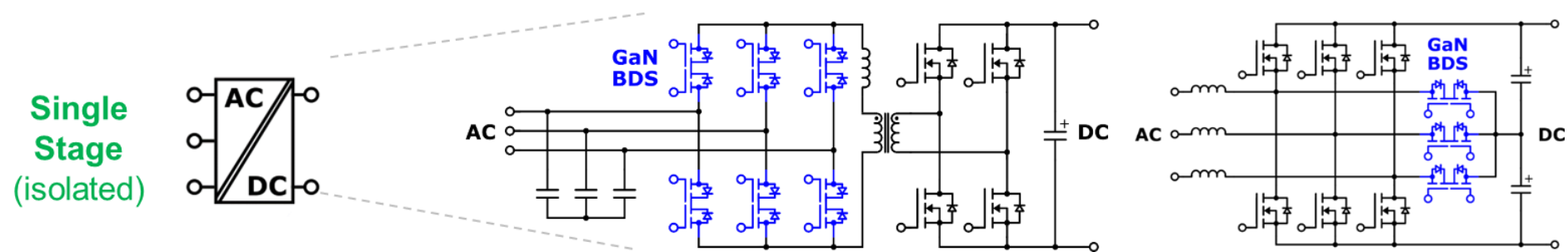
BIDIRECTIONAL GAN ENABLES SINGLE-STAGE CONVERTERS



Bi-Directional GaN enables
Single-Stage Power Conversion

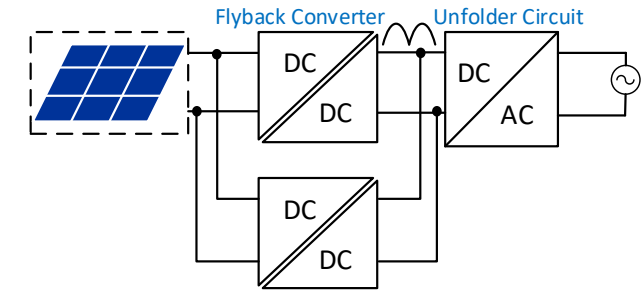


- Reduced System BoM and Cost
- Higher Conversion Efficiency

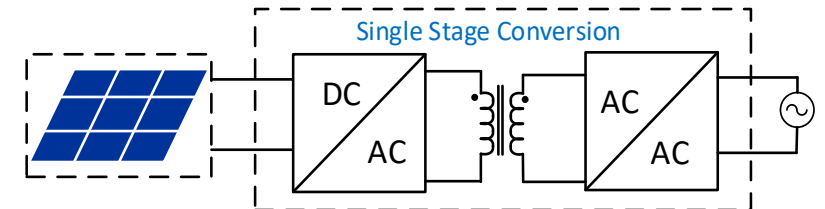


BDS GAN REDUCING NUMBER OF CONVERSION STAGES - MICROINVERTER

- **Minimizing Power Conversion stages to:**
 - reduce the BOM size and cost
 - increase the power density
 - maximize the system efficiency
- Today most common solution for Microinverter consists of one or multiple **Flyback converter stages followed by unfolder DC-AC converter**
 - **Disadvantages:**
 - poor efficiency figures
 - higher BOM size and cost
 - low power density compared to most advanced/trending topologies
- Future trend focuses on **DAB based single stage solutions.**
 - **Advantages:**
 - improving BOM cost and size
 - system Efficiency and power density.



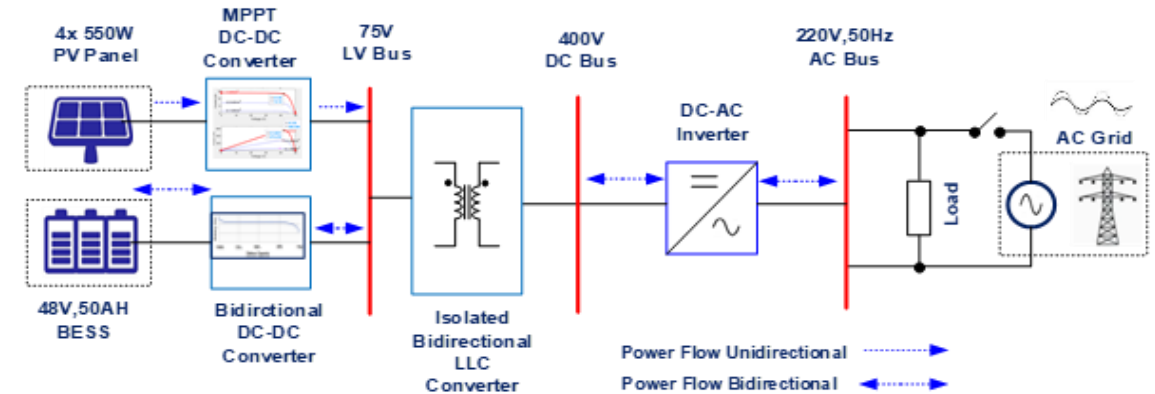
Flyback + unfolder based Microinverter



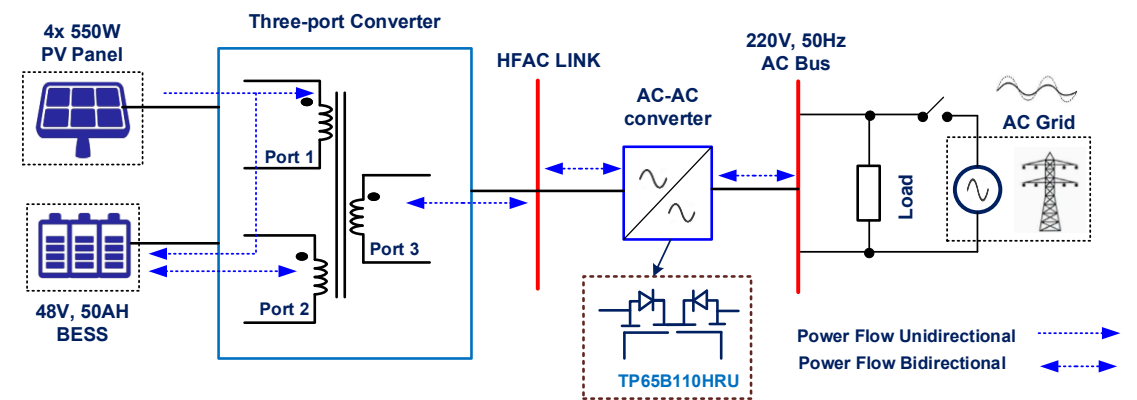
Single stage DAB based Microinverter

BDS GAN REDUCING NUMBER OF CONVERSION STAGES – HYBRID INVERTER

- **Minimizing Power Conversion stages to:**
 - reduce the BOM size and cost
 - increase the power density
 - maximize the system efficiency
- Today most common solution for Hybrid-Inverter consists of Intermediate Bus architecture, with multiple DC Bus, first from PV and ESS to ~75V, second 400V HV isolated rail
 - **Disadvantages:**
 - Multiple power conversions lower system efficiency
 - higher BOM size and cost
 - low power density compared to most advanced/trending topologies
- Future trend focuses on **Multiport single DC-DC stage solutions.**
 - **Advantages:**
 - improving BOM cost and size
 - Increasing system Efficiency and power density.



Intermediate Bus- based Hybrid Inverter



Multiport Hybrid inverter

BDS GAN BASED MICROINVERTER

RENESAS



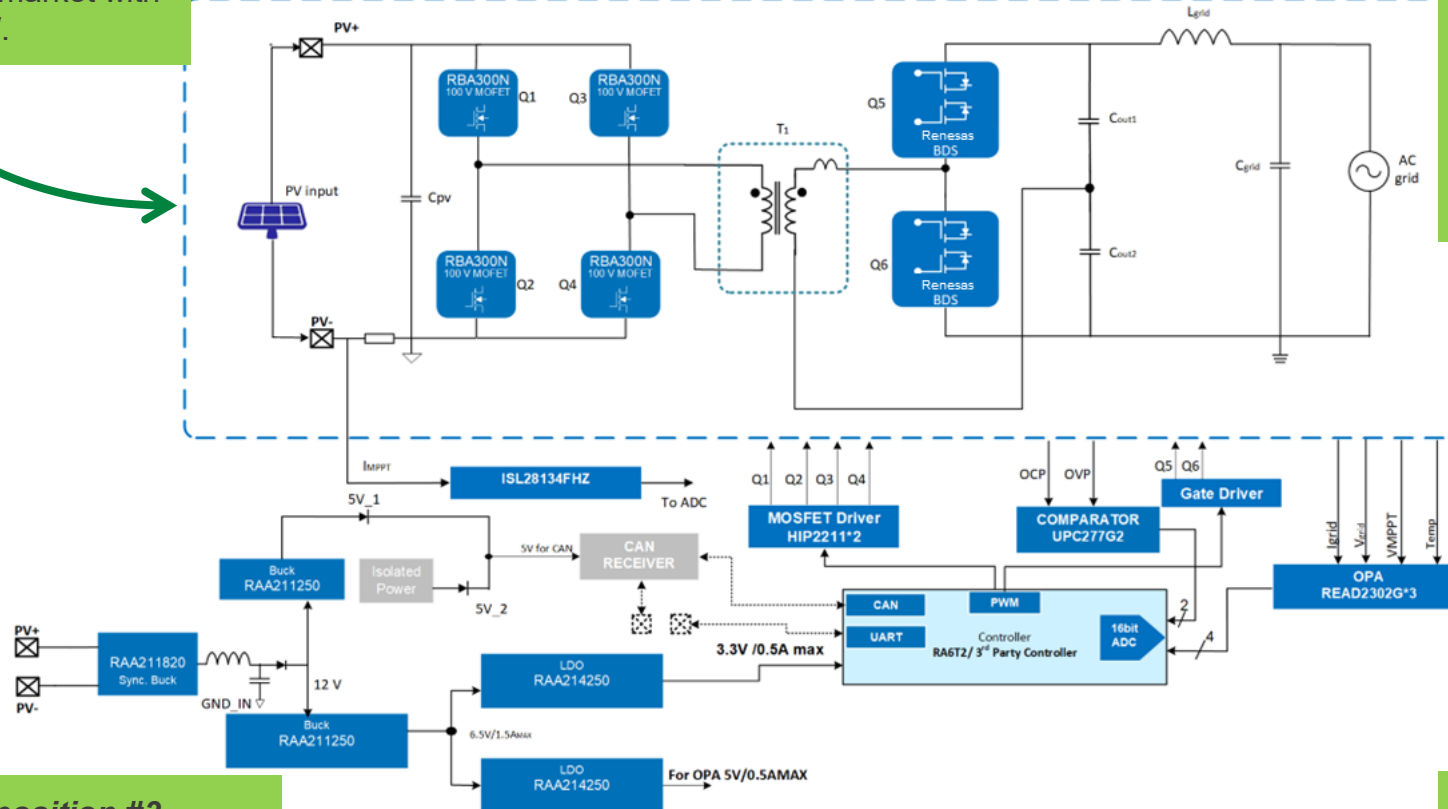
500W DAB-BASED MICROINVERTER: SYSTEM BLOCK DIAGRAM

Value Proposition #1

Faster solution to market with Renesas HW+SW.

Value Proposition #2

- 40 % Reduction in weight and volume in comparison with Flyback based solutions.
- Reduced BOM cost with single stage conversion.
- High Efficiency operation with peak efficiency upto 97%.
- High power density >4.5 W per in³



Value Proposition #3

Compact design with Renesas GaN operating at 200 kHz to 800 kHz.

Value Proposition #4

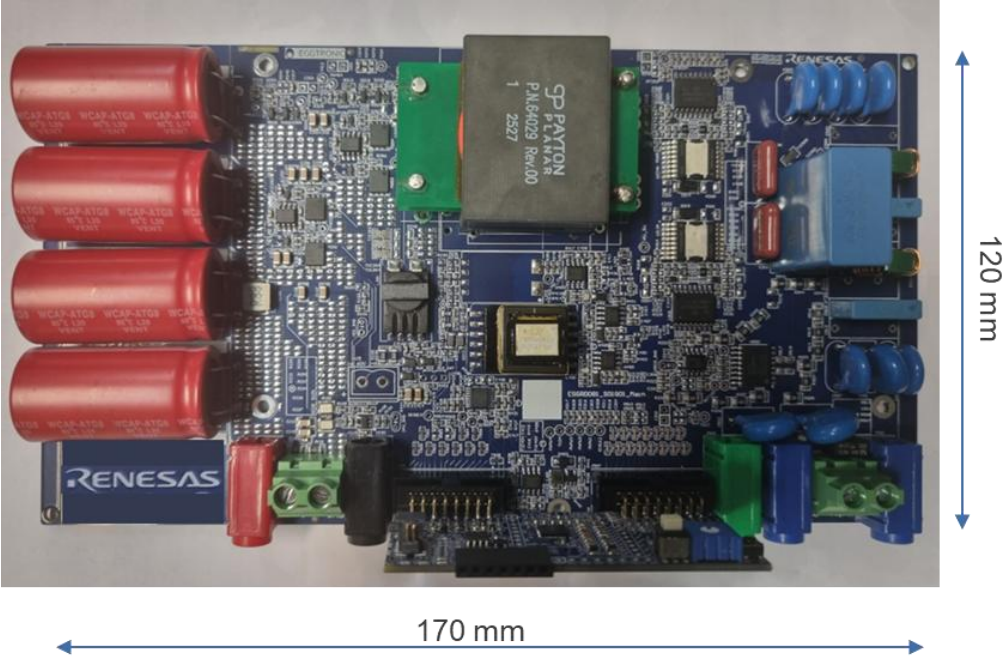
Single stage low power solution serving residential on grid/ off grid loads.

500W MICROINVERTER PROTOTYPE WITH BDS GAN AND 80V REXFET

Single Stage Microinverter Prototype Features

- DAB-based topology capable of operating in on grid/off grid mode through Single PV panel as a source.
- Operates with high efficiency (Target peak efficiency: 97%).
- High F_{SW} operation ensures compact Magnetics and ensures high power density.
- Zero Voltage Switching (ZVS) operation throughout the operating range.
- Low Ron REXFET forms primary bridge and GaN BDS forms the AC-AC secondary bridge network.
- Includes Over current protection, over voltage protection, over temperature protection.
- Improved Efficiency at light load with burst mode operation.

Specifications	
VAC	1 phase, 240VAC rms
IAC	2.2A rms
Power	500 W
Switching Frequency	200 kHz to 800 kHz
Controller	RA6T2 or EPIC2 (Eggtronic)

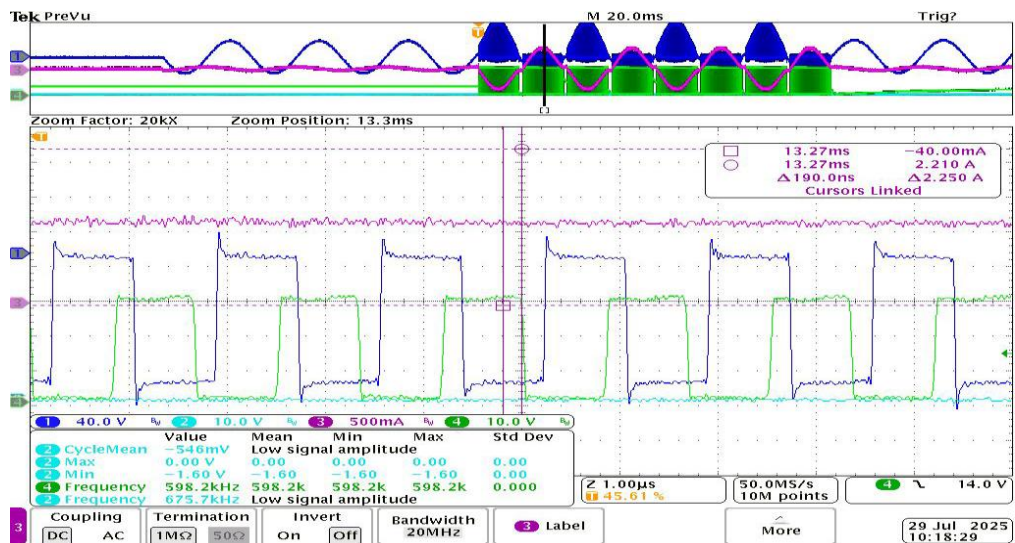


Renesas Power BoM	
TP65B110HRU	650V BDS GaN, 140mΩ, TOLT
RBE024xxxxx	80/100V REXFET MOSFET
HIP2210	100V, 3A Source, 4A Sink, High Frequency Half-Bridge Drivers
RAA211820	Integrated FET 75V, 2A Synchronous Buck Regulator
RAA211250	Integrated FET 30V, 5A Synchronous Buck Regulator

500W MICROINVERTER POC PERFORMANCES

Microinverter Switching Waveforms

Transformer Secondary Voltage (Blue); Grid Current (Magenta), Primary MOSFET switching signal (Green)

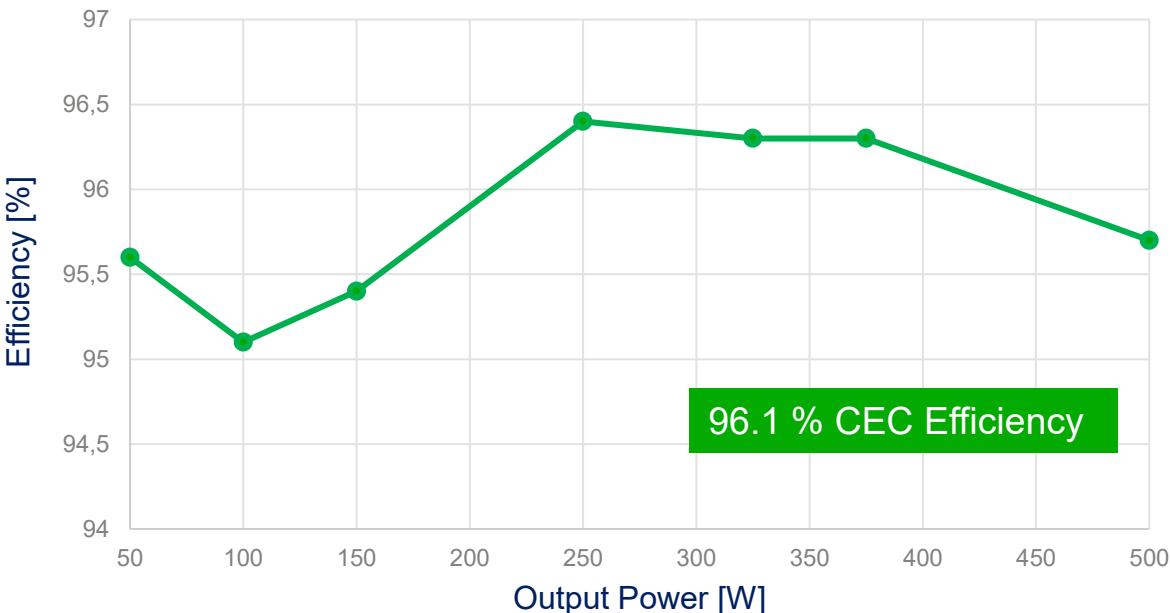


- PLL is synched with grid, with observable transformer secondary voltage.
- Phase shift is maintained between primary and secondary bridges to deliver required power to the grid.
- The switching frequency is varied from 200 kHz to 800 kHz to reduce the harmonics and maintain the continuous conduction even at zero crossing.
- GaN BDS enables high frequency operation achieving high power density

Preliminary Efficiency Measurements

Single-Stage converter efficiency outperforms existing dual-stage solutions

Microinverter Efficiency @ $V_{IN} = 35 V_{DC}$, $V_{OUT} = 240 V_{AC}$



Preliminary Results:

the ongoing optimization process is expected to further improve efficiency performance

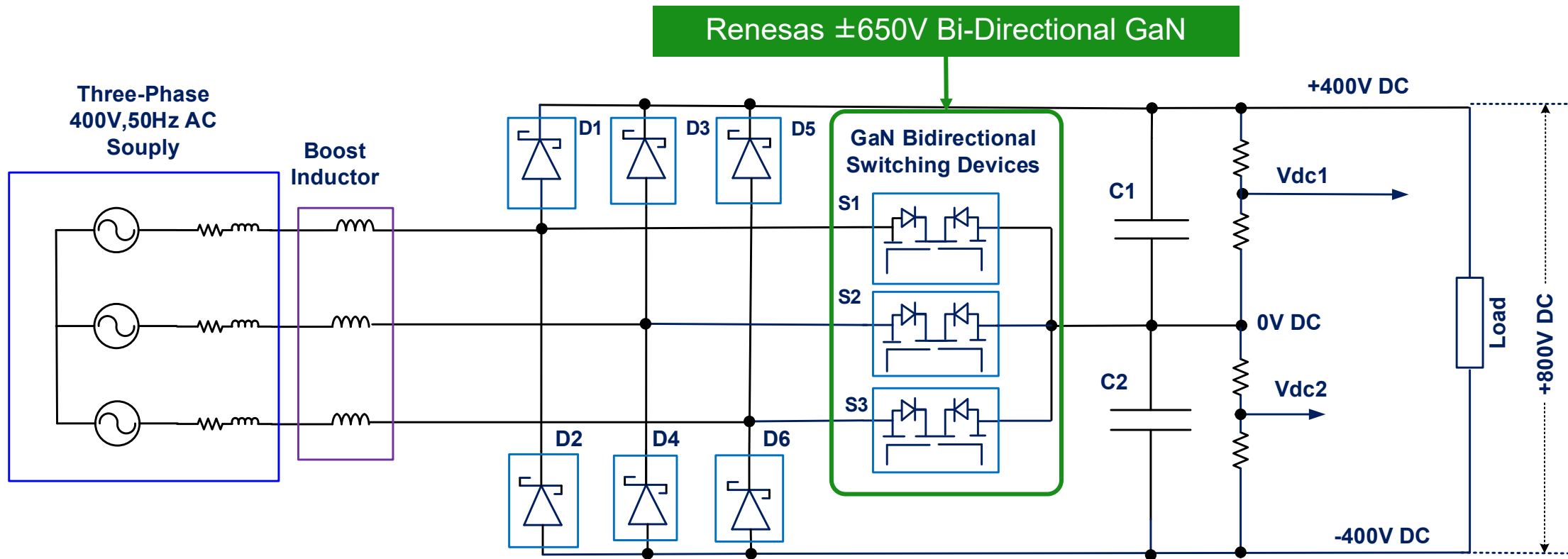
BDS GAN BASED VIENNA RECTIFIER

RENESAS



3-PH VIENNA RECTIFIER: TOPOLOGY OVERVIEW

- Vienna rectifier is a unidirectional three-level AC-DC converter, which is widely used in AC-DC PFC applications.
- Three bidirectional GaN switches one per phase employing two gates.
- Voltage stress on the power switches is only half of the output voltage.
- A single GaN BDS device replace 2x switches in back-to-back configuration, reducing BoM size and cost

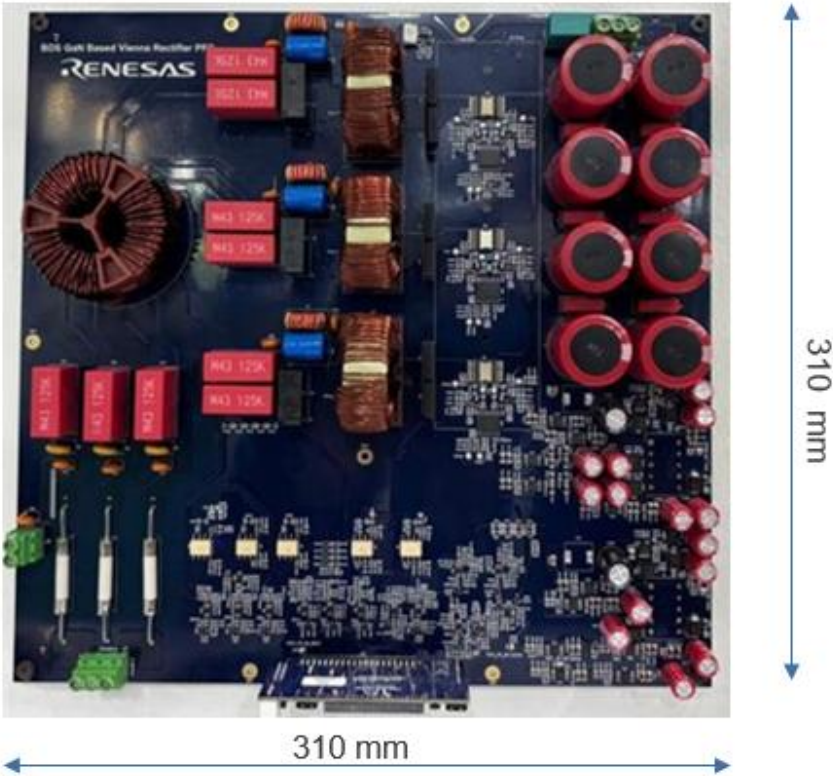


3.6 KW VIENNA RECTIFIER PROTOTYPE WITH BDS GAN

Vienna Rectifier Prototype Features

- The Vienna Rectifier is a non-isolated PFC converter which rectifies a 3ph AC Input to a $\pm 400V$ or $800V$ DC Bus
- This PoC delivers up to 3.6 kW power to the DC Bus in a compact form factor. Higher power can be achieved by exploiting lower $R_{ds,on}$ BDS GaN device
- Bi-Directional HV GaN devices replace the back-to-back structure by enhancing system performance while reducing BoM size and cost
- The RX26T Renesas core MCU is used as Digital Power Controller
- Switching frequency up to 100kHz w/ cycle-by-cycle PWM update
- RX26T includes fast analog comparators for fast current protection
- Enhanced reliability guarantee by single BDS GaN device

Specifications	
VAC	3 phase, 460 VAC rms
IAC	2.2A rms
Output Power	3.6 kW
Switching Frequency	Up to 100 kHz
Controller	RX26T (Renesas-Core MCU)



Renesas Power BoM	
TP65B110HRU	650V BDS GaN, 140mΩ, TOLT
RAA223021	700V AC/DC Regulator with Ultra-Low Standby Power and up to 12W Output Power
RAA214250	20V, 500 mA, Linear Regulator

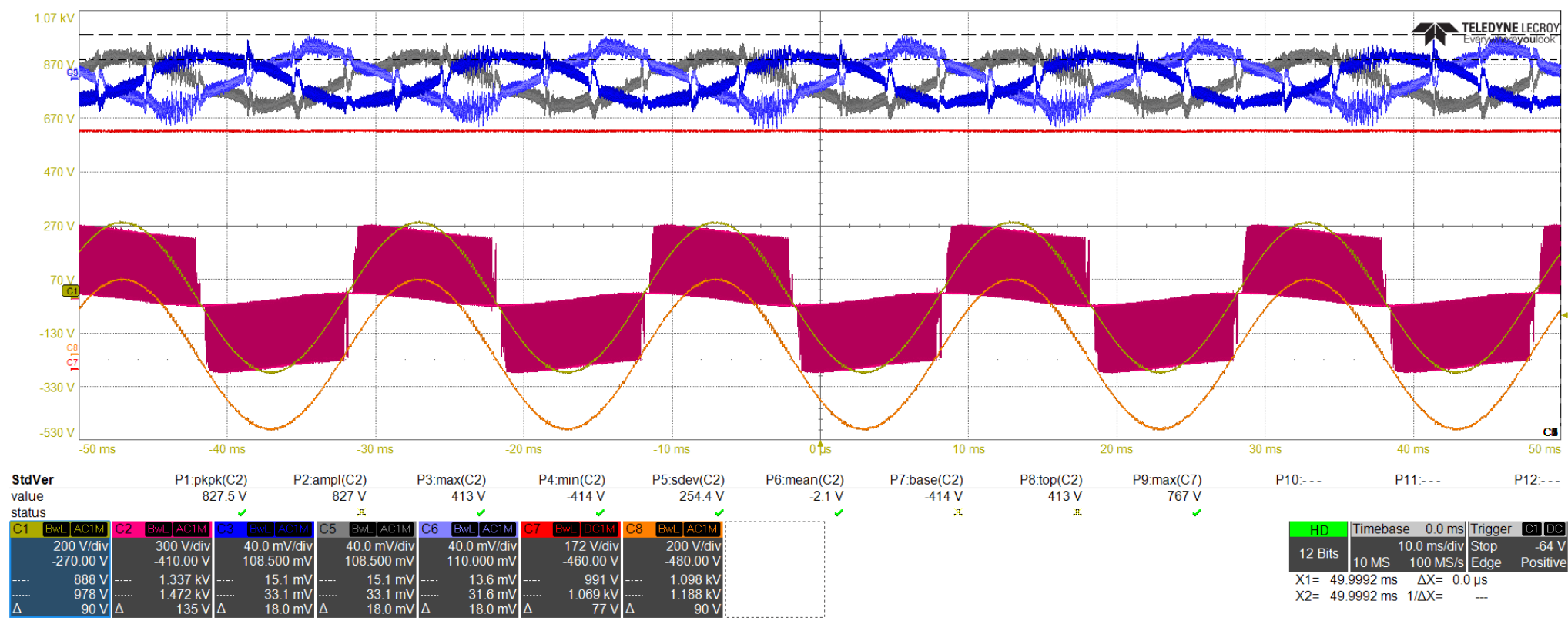
3-PH VIENNA RECTIFIER: SWITCHING WAVEFORMS

Switch voltage (phase A), Supply voltage (phase A)

DC Bus voltage (Closed loop operation)

i_IN,PhaseA, i_IN,PhaseB, i_IN,PhaseC

Preliminary Results:
Control Loop optimization ongoing



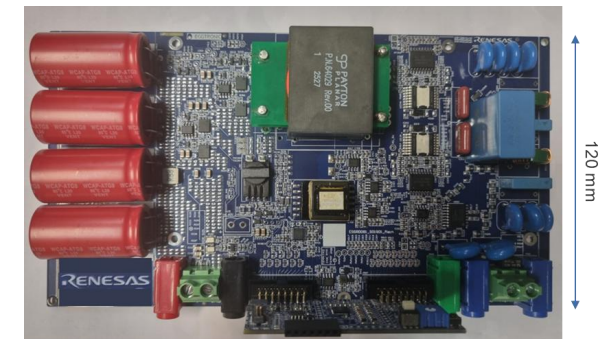
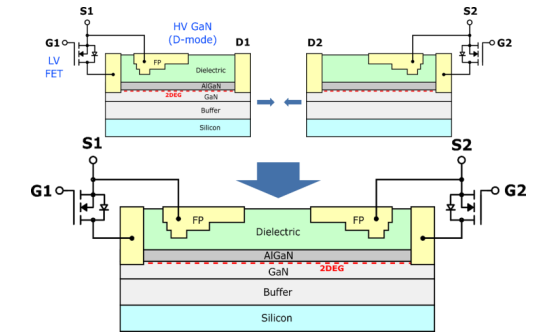
CONCLUSION

RENESAS



CONCLUSION

- Power Conversion System Design and Definition is moving towards smaller, highly efficient solutions, hence increasing power density while reducing losses
- Renesas $\pm 650\text{V}$ Bidirectional GaN switch allows single-stage topologies, supporting system designers meeting today's and future challenges
- **Renesas Bi-Directional GaN technology enables Microinverter, Hybrid-Inverter, Vienna Rectifier and Single-Stage OBC architectures that outperforms existing solutions in terms of efficiency and power density**
- **Future Work:**
 - Optimize Microinverter design aiming at further enhancing efficiency
 - Optimize Vienna Rectifier Performance
 - Proof the advantages of Single-Stage topologies in other applications, such as OBC



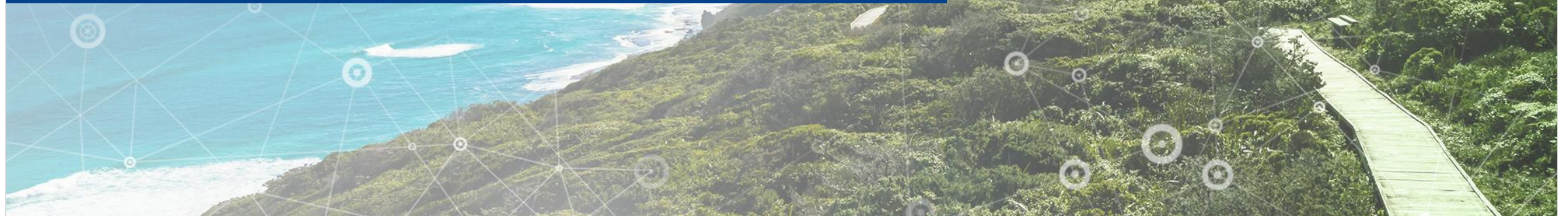
THANK YOU!

"Investing in renewable energies is investing in a bright future."

- Anonymous



RENESAS



REFERENCES

- [1] D. Bisi, "GaN Bidirectional Switches: Present & Future", APEC 2025.
- [2] L. Schrittwieser, M. Leibl, J. W. Kolar, "99% Efficient Isolated Three-Phase Matrix-Type DAB Buck–Boost PFC Rectifier," *IEEE Transactions on Power Electronics* 35, pages 138-157, 2020.
- [3] F. Vollmaier, N. Nain, J. Huber, J. W. Kolar, K. K. Leong, B. Pandya "Performance Evaluation of Future T-Type PFC Rectifier and Inverter Systems with Monolithic Bidirectional 600 V GaN Switches," 2021 IEEE Energy Conversion Congress and Exposition (ECCE), 10 – 14 Oct 2021.
- [4] N. Kummari, S. Chakraborty and S. Chattopadhyay, "An Isolated High-Frequency Link Microinverter Operated with Secondary-Side Modulation for Efficiency Improvement," in *IEEE Transactions on Power Electronics*, vol. 33, no. 3, pp. 2187-2200, March 2018.
- [5] A. Bhattacharjee, I. Batarseh, "A New Bidirectional AC-link Microinverter Based On Dual Active Bridge Topology," 2019 IEEE Applied Power Electronics Conference and Exposition (APEC), 17-21 March 2019, Anaheim, CA.
- [6] M. A. Rezaei, K. -J. Lee and A. Q. Huang, "A High-Efficiency Flyback Micro-inverter With a New Adaptive Snubber for Photovoltaic Applications
- [7] Choi, Y.-G.; Lee, H.-S.; Kang, B.; Lee, S.-C.; Yoon, S.-J. Compact Single-Stage Micro-Inverter with Advanced Control Schemes for Photovoltaic Systems. *Energies* **2019**, *12*, 1234. <https://doi.org/10.3390/en12071234>
- [8] Q. Yang, J. Yang and R. Li, "Analysis of Grid Current Distortion and Waveform Improvement Methods of Dual-Active-Bridge Microinverter," in *IEEE Transactions on Power Electronics*, vol. 38, no. 4, pp. 4345-4359, April 2023.
- [9] Nagesha Chitpadi, [Single Stage Microinverter Topology: A Full System Design Solution for both On/Off-Grid applications](#)
- [10] Ravichandran C, [A PV and Battery Energy Storage Based-Hybrid Inverter Architecture Addressing Future Energy Demands](#)

[Renesas.com](https://www.renesas.com)